1SS301CCW

SILICON EPITAXIAL PLANAR DIODE

Applications

• Ultra high speed switching





SOT-323 Plastic Package Marking Code: PH

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Maximum (Peak) Reverse Voltage	V_{RM}	85	V
Reverse Voltage	V_R	80	V
Average Forward Current	Io	100	mA
Maximum (Peak) Forward Current	I _{FM}	300	mA
Peak Forward Surge Current (t _p = 10 ms)	I _{FSM}	2	А
Total Power Dissipation	P _{tot}	200	mW
Junction Temperature	TJ	125	°C
Storage Temperature Range	T _s	- 55 to + 125	°C

Characteristics at $T_a = 25$ °C

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at I _F = 100 mA	V _F	-	1.2	V
Reverse Current at $V_R = 30 \text{ V}$ at $V_R = 80 \text{ V}$	I _R		0.1 0.5	μА
Total Capacitance at $V_R = 0$, $f = 1$ MHz	Ст	-	3	pF
Reverse Recovery Time at I_F = 10 mA, V_R = 6 V, I_{rr} = 1 mA, R_L = 100 Ω	t _{rr}	-	4	ns



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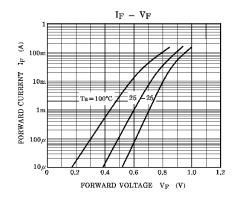
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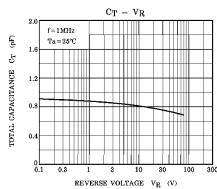


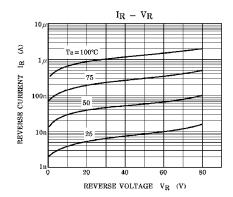


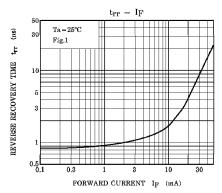


Dated: 10/10/2008











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